

FIG. 1

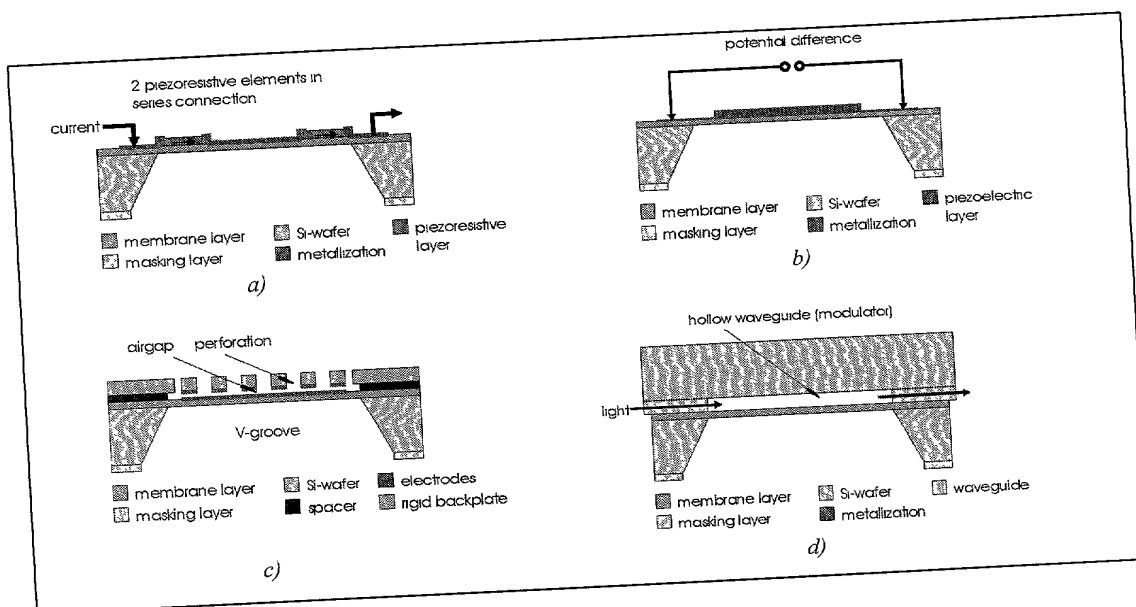
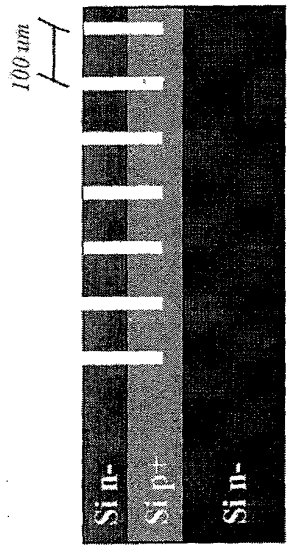
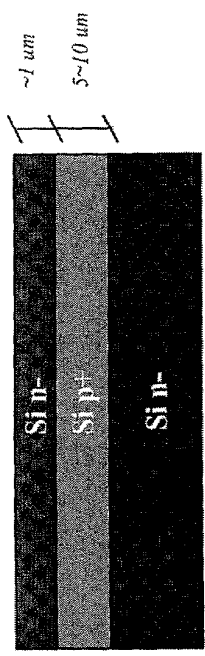


FIG. 2



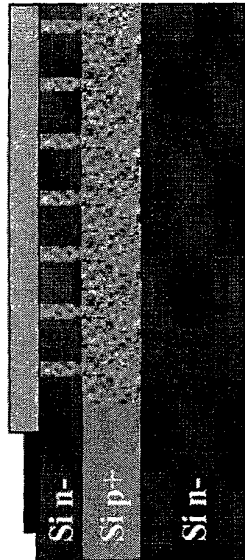
2. Trench formation by plasma etching (and mask opening)

FIG. 3B



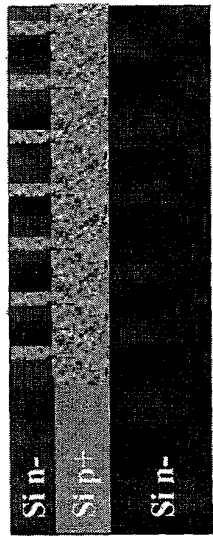
1. Si p+/n- epi layers on substrate

FIG. 3A



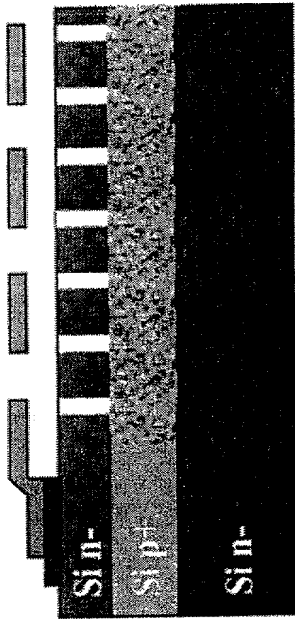
5. Deposition and patterning of the sacrificial layer
6. Nitride isolation layer

FIG. 3D



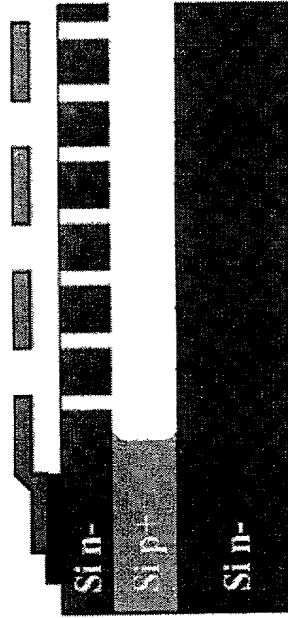
3. Si Porous formation in p+ by electrochemical attack
4. Trench filling and surface planarization

FIG. 3C



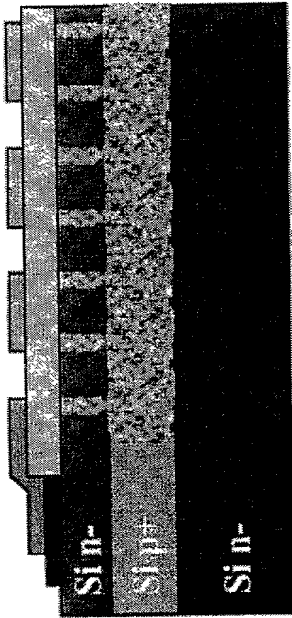
8. Removal of the sacrificial layer (HF attack)

FIG. 3F



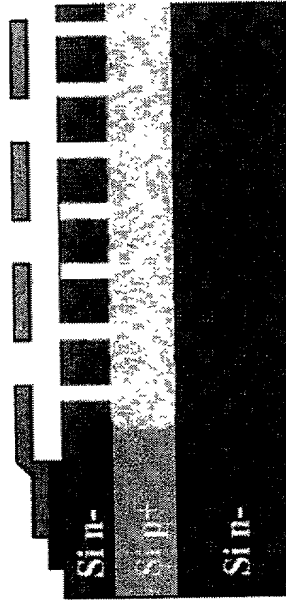
10. Removal of Si-porous

FIG. 3H



7. PoliSi n+ formation for backplate

FIG. 3E



9. Si-porous Oxidation

FIG. 3G

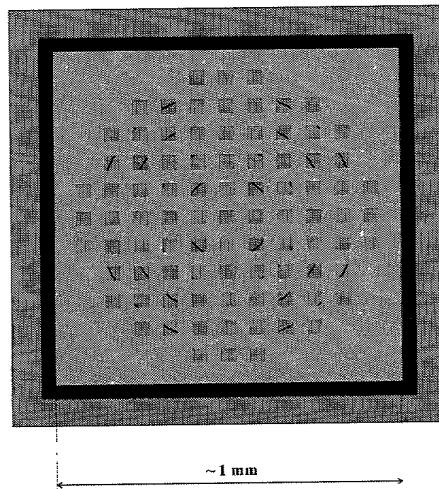


FIG. 4

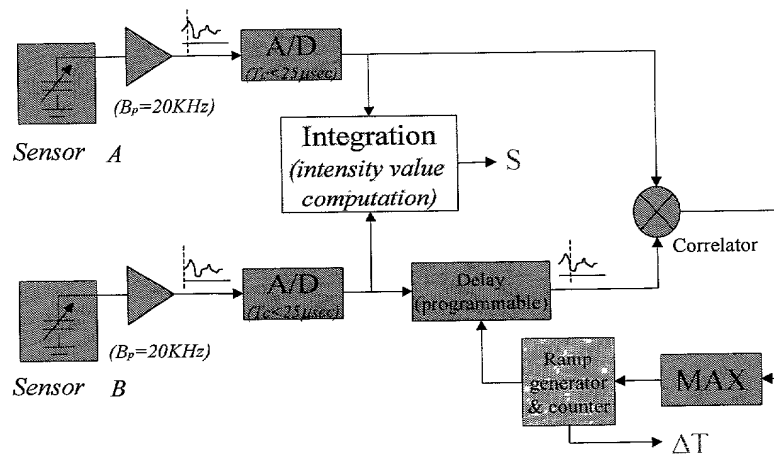


FIG. 5